

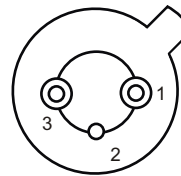
Silicon Photodiode 1.25 Gbps

Features of Diode

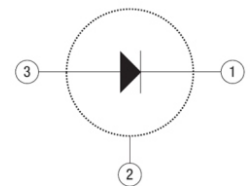
- Silicon Photodiodes
- High Responsivity
- Large Diameter Sensing Area
- Low Capacitance @ 3.3 V



PINOUT



Bottom view



Functional Schematic

Absolute maximum ratings

Parameter	Min.	Max.
Storage temperature	-55 °C	125 °C
Operating temperature	-40 °C	75 °C
Reverse voltage		20 V

Number	Function
1	Cathode
2	Case
3	Anode

Electrical-optical characteristics

Parameter Laser Diode	Test Condition	Min.	Typ.	Max.
Active area diameter			150 µm	
Responsivity	= 850 nm		0.36 A/W	
Dark current	$V_R = 3.3 \text{ V}$		20 pA	500 pA
Detection range			850 nm	
Rise time	20- 80 %, $R_L = 53 \quad V_R = 3.3 \text{ V}$		38 ps	
Fall time	80- 20 %, $R_L = 53 \quad V_R = 3.3 \text{ V}$		313 ps	
NEP in $\text{W/Hz}^{1/2}$			8.60×10^{-15}	
Possible receptacle (type A)	ST1, ST2, ST4, P2, LC, SC, FC1, FC2, Fiberdip, SMA1, SMA2			

Compliant with RoHS-requirements (2002/95/EG vom 27.01.2003)

Note: The above product specifications are subject to change without notice.